

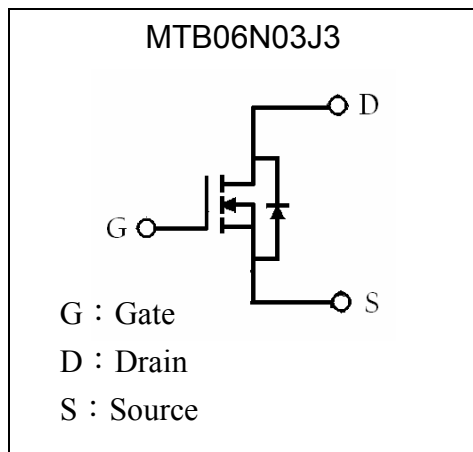
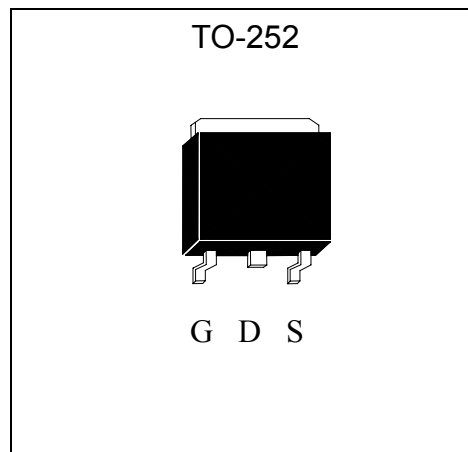
**N-Channel Enhancement Mode Power MOSFET**

# MTB06N03J3

$BV_{DSS}$	30V
$I_D$	80A
$R_{DS(ON)}$	6m $\Omega$

**Features**

- 100% UIS testing, @ $V_D=15V$ ,  $L=0.1mH$ ,  $V_G=10V$ ,  $I_L=40V$ , rated  $V_{DS}=25V$  N-CH
- Simple Drive Requirement
- Repetitive Avalanche Rated
- Fast Switching Characteristic
- RoHS compliant package & Halogen-free package

**Symbol**

**Outline**

**Absolute Maximum Ratings** ( $T_c=25^\circ C$ , unless otherwise noted)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current @ $T_c=25^\circ C$	$I_D$	80	A
Continuous Drain Current @ $T_c=100^\circ C$	$I_D$	50	
Pulsed Drain Current (Note 1)	$I_{DM}$	170	
Avalanche Current	$I_{AS}$	53	
Avalanche Energy @ $L=0.1mH$ , $I_D=53A$ , $R_G=25\Omega$	$E_{AS}$	140	mJ
Repetitive Avalanche Energy @ $L=0.05mH$ (Note 2)	$E_{AR}$	40	
Total Power Dissipation @ $T_c=25^\circ C$	$P_d$	83	W
Total Power Dissipation @ $T_c=100^\circ C$		45	
Operating Junction and Storage Temperature Range	$T_j, T_{stg}$	-55~+175	$^\circ C$

Note : 1. Pulse width limited by maximum junction temperature  
 2. Duty cycle  $\leq 1\%$



**Thermal Data**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R <sub>th,j-c</sub>	1.8	°C/W
Thermal Resistance, Junction-to-ambient, max	R <sub>th,j-a</sub>	75	°C/W

**Characteristics (T<sub>c</sub>=25°C, unless otherwise specified)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
<b>Static</b>					
BV <sub>DSS</sub>	30	-	-	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA
V <sub>GS(th)</sub>	1	1.5	3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA
I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> =±20, V <sub>DS</sub> =0V
I <sub>DSS</sub>	-	-	1	μA	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V
	-	-	25		V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, T <sub>j</sub> =125°C
*I <sub>D(ON)</sub>	80	-	-	A	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V
*R <sub>DS(ON)</sub>	-	5.3	6	mΩ	V <sub>GS</sub> =10V, I <sub>D</sub> =30A
	-	7.6	9.5		V <sub>GS</sub> =5V, I <sub>D</sub> =24A
*G <sub>FS</sub>	-	25	-	S	V <sub>DS</sub> =5V, I <sub>D</sub> =24A
<b>Dynamic</b>					
*Q <sub>g</sub> (V <sub>GS</sub> =10V)	-	53	-	nC	I <sub>D</sub> =30A, V <sub>DS</sub> =15V, V <sub>GS</sub> =10V
*Q <sub>g</sub> (V <sub>GS</sub> =5V)	-	30	-		
*Q <sub>gs</sub>	-	8	-		
*Q <sub>gd</sub>	-	17	-	ns	V <sub>DS</sub> =15V, I <sub>D</sub> =25A, V <sub>GS</sub> =10V, R <sub>GS</sub> =2.7Ω
*t <sub>d(ON)</sub>	-	22	-		
*t <sub>r</sub>	-	16	-		
*t <sub>d(OFF)</sub>	-	65	-		
*t <sub>f</sub>	-	10	-	pF	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz
C <sub>iss</sub>	-	4753	-		
C <sub>oss</sub>	-	495	-		
C <sub>rss</sub>	-	348	-		
R <sub>g</sub>	-	1.2	-	Ω	V <sub>GS</sub> =15mV, V <sub>DS</sub> =0V, f=1MHz
<b>Source-Drain Diode</b>					
*I <sub>S</sub>	-	-	80	A	
*I <sub>SM</sub>	-	-	170		
*V <sub>SD</sub>	-	-	1.3	V	I <sub>F</sub> =I <sub>S</sub> , V <sub>GS</sub> =0V
*t <sub>rr</sub>	-	32	-	ns	I <sub>F</sub> =I <sub>S</sub> , V <sub>GS</sub> =0, dI <sub>F</sub> /dt=100A/μs
*Q <sub>rr</sub>	-	12	-	nC	

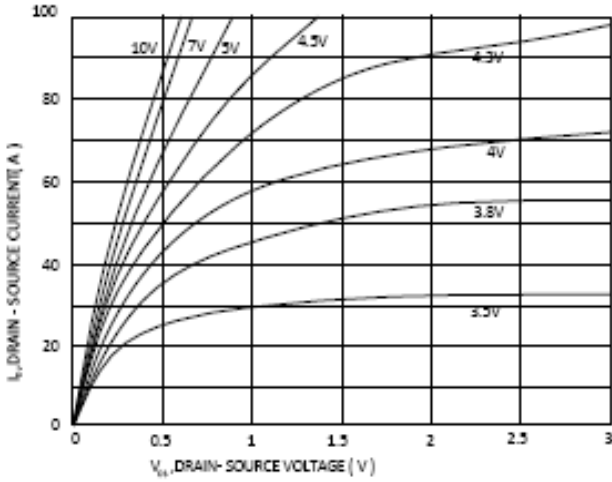
\*Pulse Test : Pulse Width ≤300μs, Duty Cycles ≤2%

**Ordering Information**

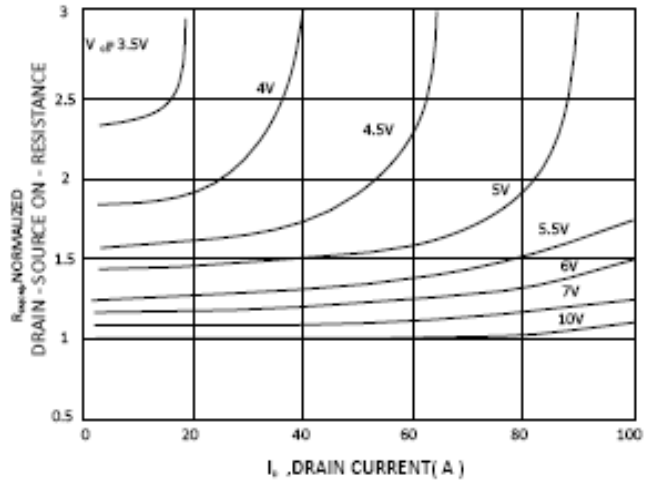
Device	Package	Shipping	Marking
MTB06N03J3	TO-252 (RoHS compliant & Halogen-free)	2500 pcs / Tape & Reel	B06N03

**Characteristic Curves**

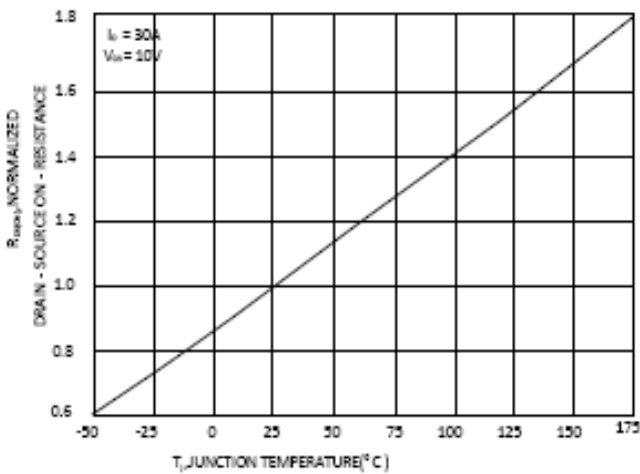
ON-REGION CHARACTERISTIC



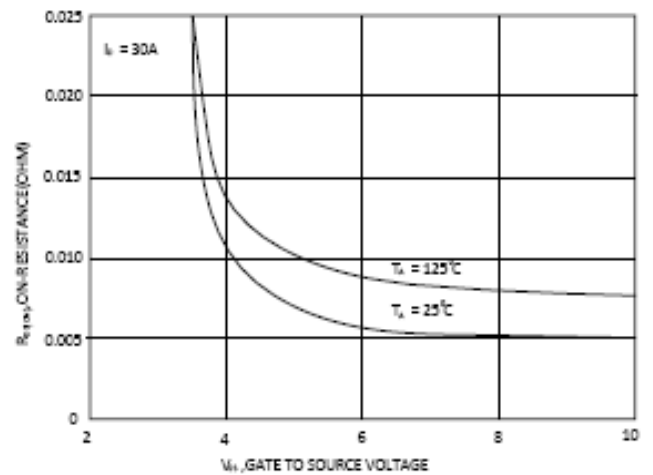
ON- RESISTANCE VARIATION WITH DRAIN CURRENT AND GATE VOLTAGE



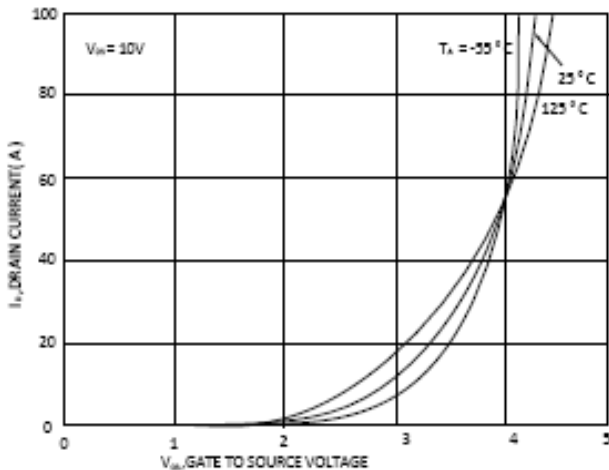
ON- RESISTANCE VARIATION WITH TEMPERATURE



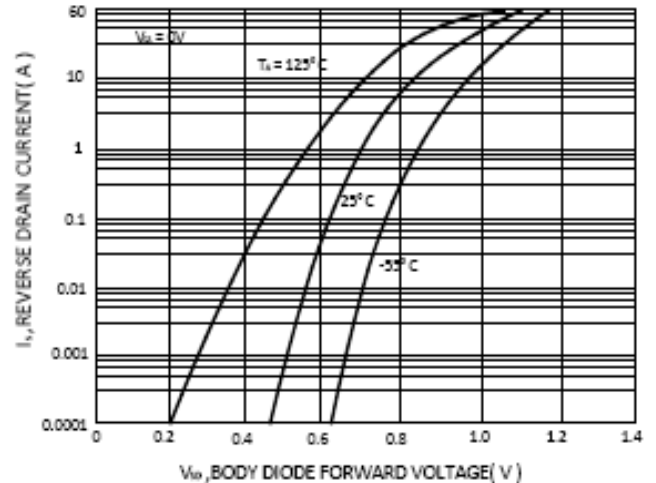
ON-RESISTANCE VARIATION WITH GATE-TO-SOURCE VOLTAGE



TRANSFER CHARACTERISTICS

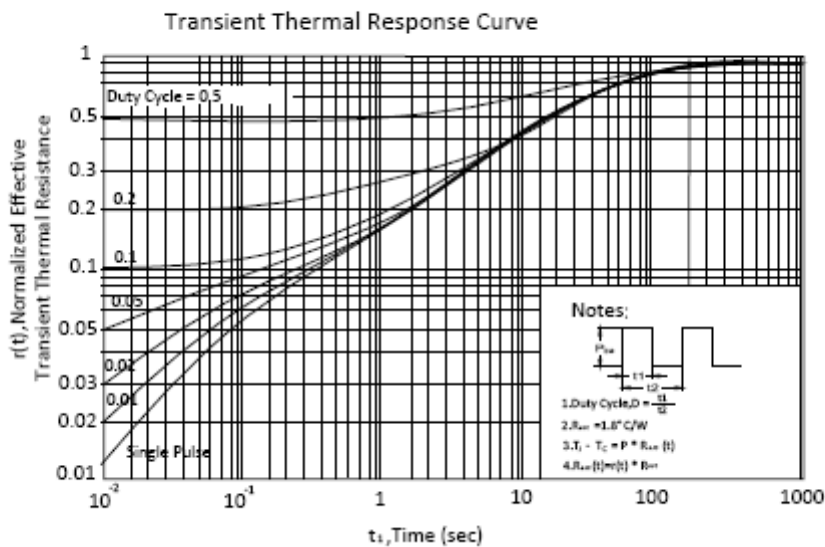
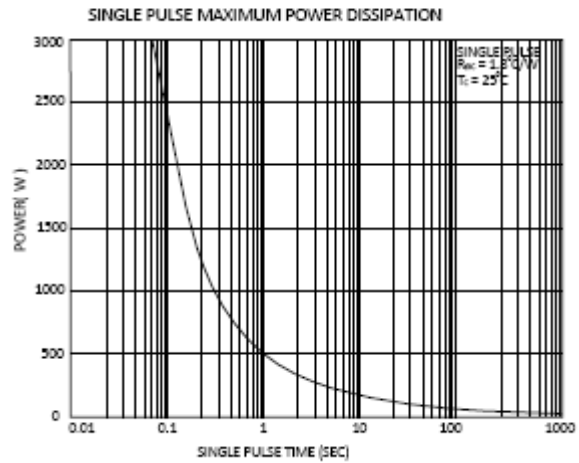
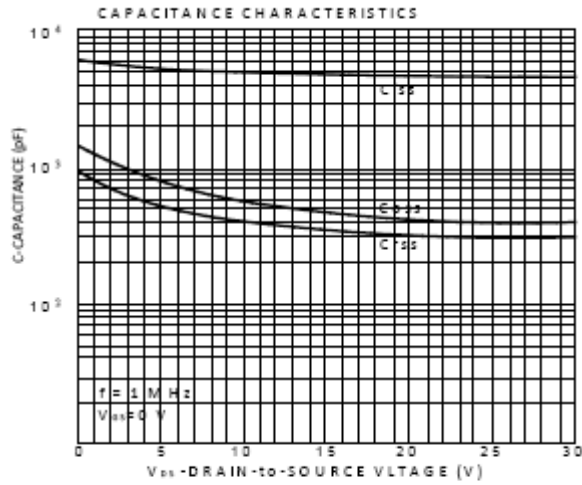
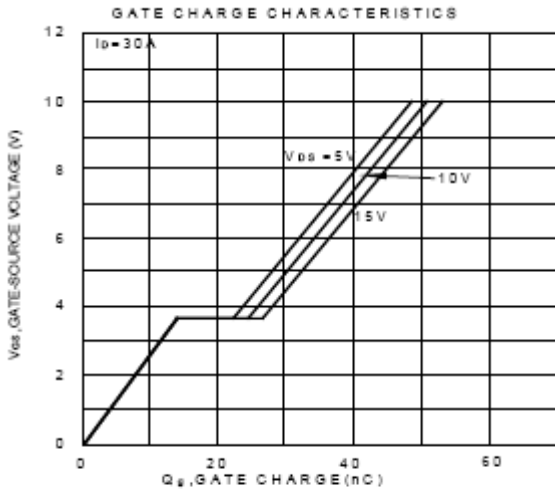


BODY DIODE FORWARD VOLTAGE VARIATION WITH SOURCE CURRENT AND TEMPERATURE

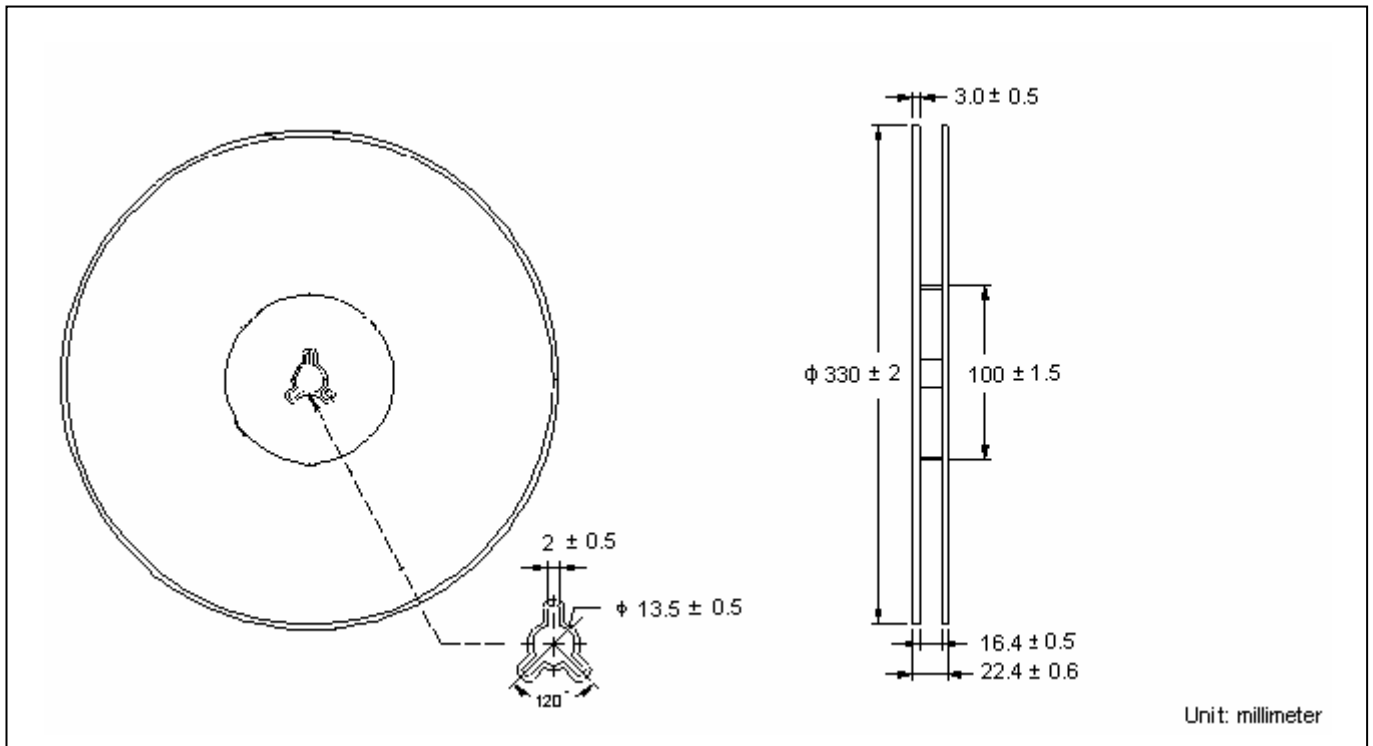




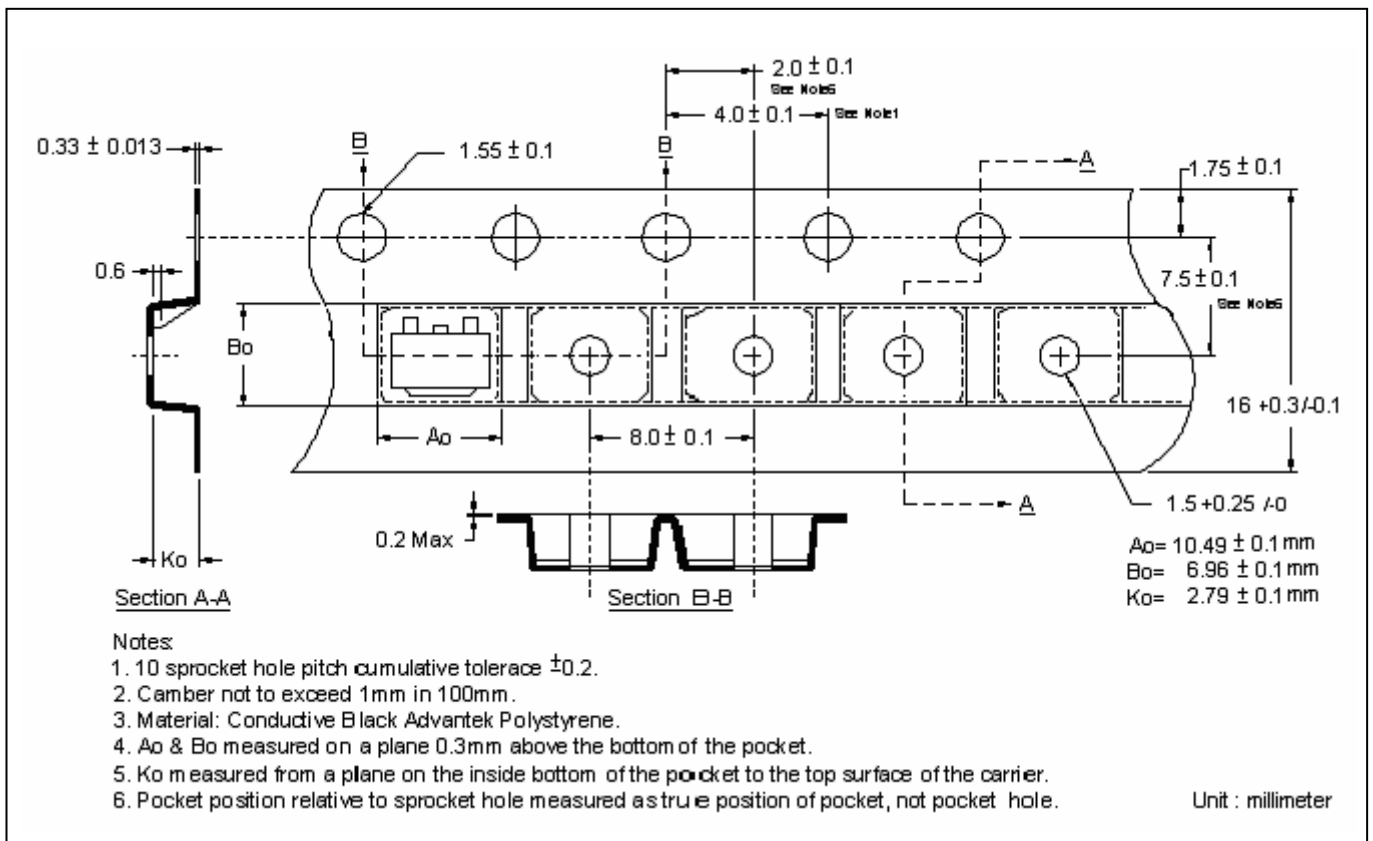
**Characteristic Curves(Cont.)**



### Reel Dimension



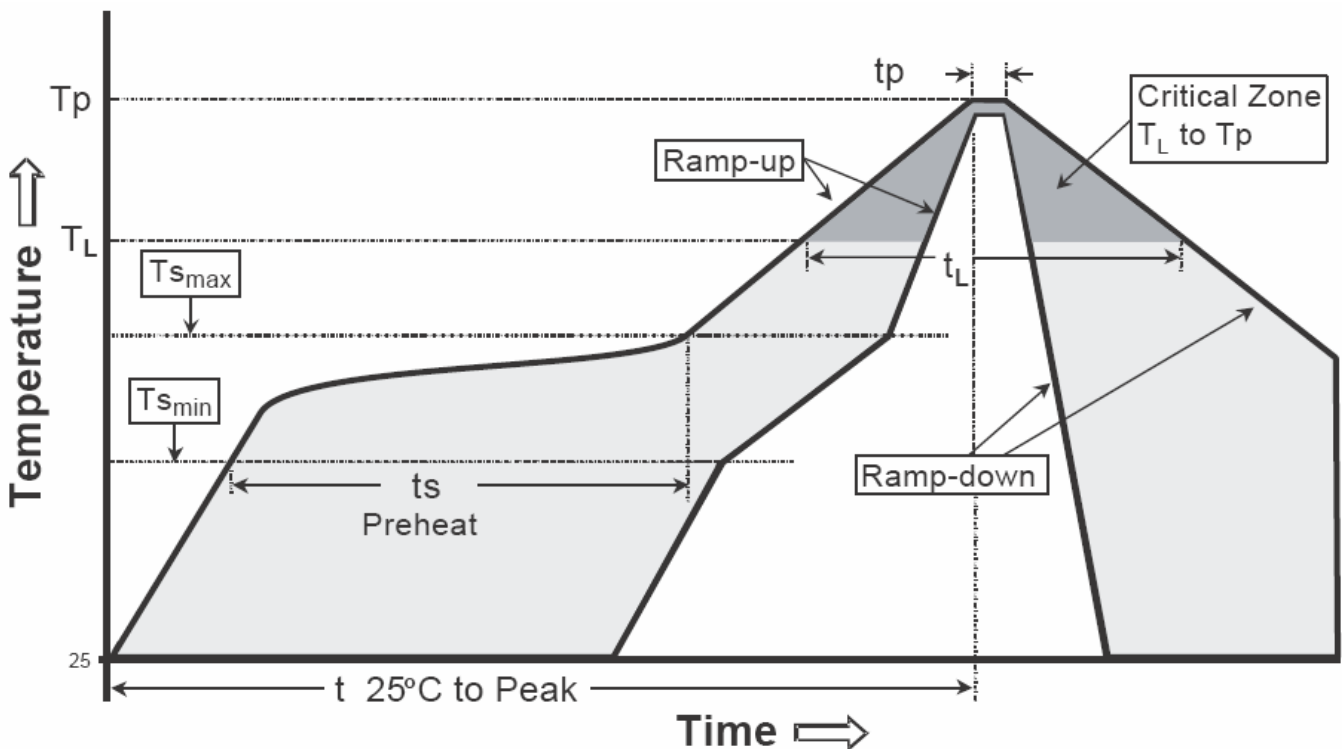
### Carrier Tape Dimension



**Recommended wave soldering condition**

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

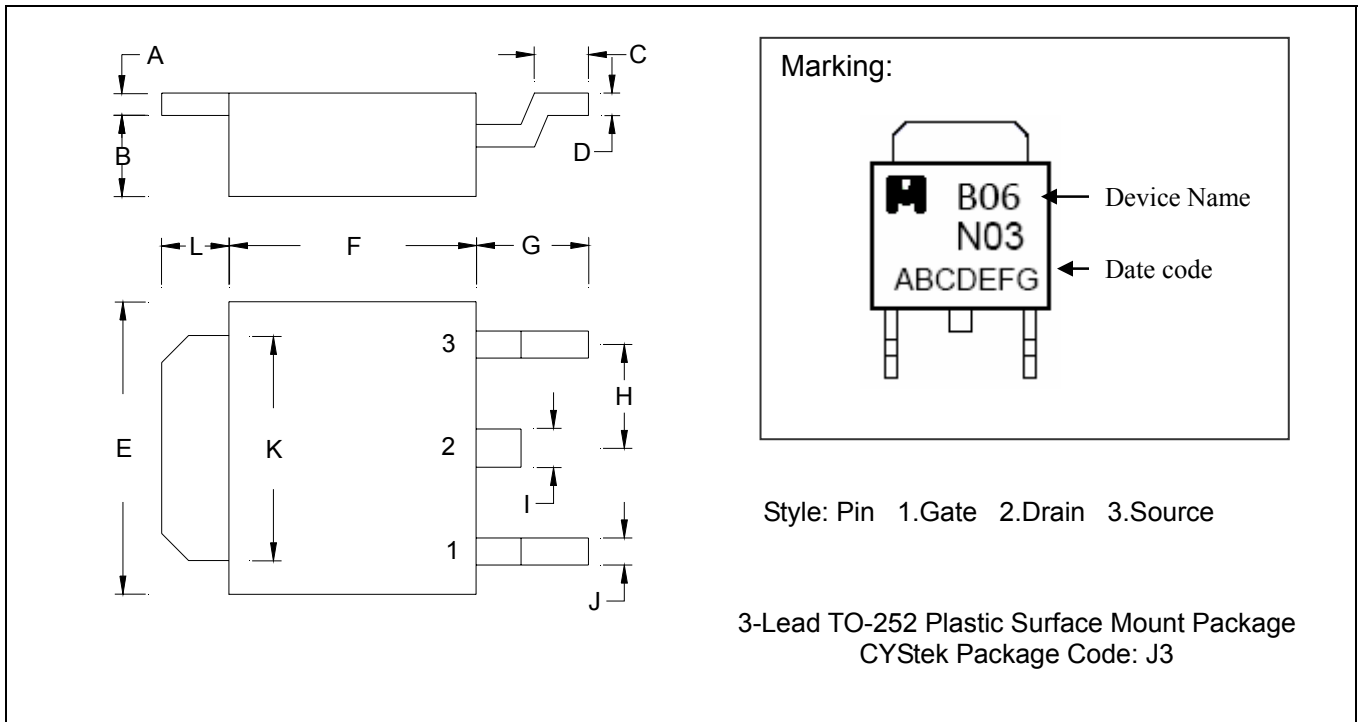
**Recommended temperature profile for IR reflow**



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T <sub>smax</sub> to T <sub>p</sub> )	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T <sub>s min</sub> )	100°C	150°C
-Temperature Max(T <sub>s max</sub> )	150°C	200°C
-Time(t <sub>s min</sub> to t <sub>s max</sub> )	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T <sub>L</sub> )	183°C	217°C
- Time (t <sub>L</sub> )	60-150 seconds	60-150 seconds
Peak Temperature(T <sub>P</sub> )	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

**TO-252 Dimension**



\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0177	0.0217	0.45	0.55	G	0.0866	0.1102	2.20	2.80
B	0.0650	0.0768	1.65	1.95	H	-	*0.0906	-	*2.30
C	0.0354	0.0591	0.90	1.50	I	-	0.0449	-	1.14
D	0.0177	0.0236	0.45	0.60	J	-	0.0346	-	0.88
E	0.2441	0.2677	6.20	6.80	K	0.2047	0.2165	5.20	5.50
F	0.2125	0.2283	5.40	5.80	L	0.0551	0.0630	1.40	1.60

- Notes:**
- Controlling dimension: millimeters.
  - Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
  - If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead : KFC; pure tin plated
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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